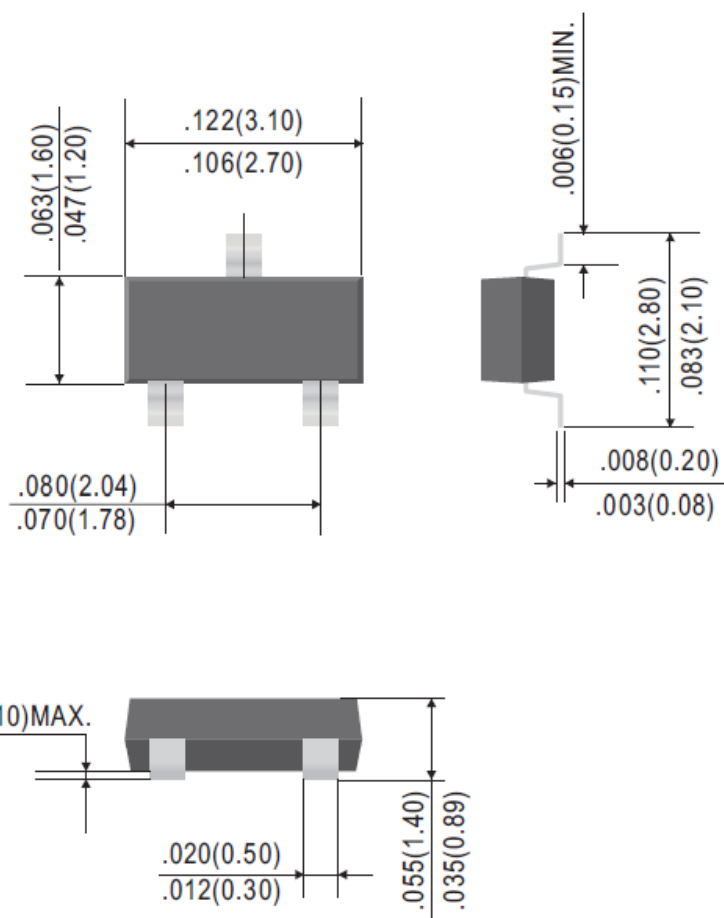




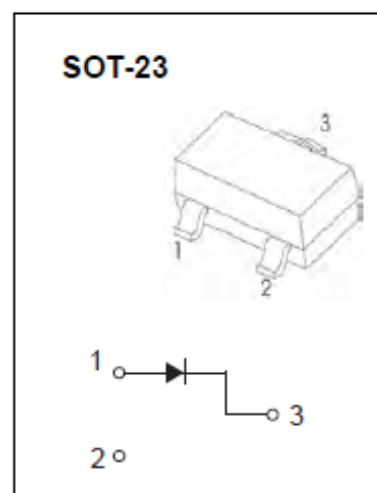
ERS411DS



Plastic-Encapsulate Diodes



Dimensions in inches and (millimeters)



SCHOTTKY BARRIER DIODE

FEATURES

- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability
- Pb-Free package is available
- RoHS product for packing code suffix "G"
- Halogen free product for packing code suffix "H"
- Moisture Sensitivity Level 1

MARKING: D3E

**ERS411DS****Plastic-Encapsulate Diodes**

Maximum Ratings ($T_a=25^{\circ}\text{C}$ unless otherwise specified)			
Parameter	Symbol	Limit	Unit
Peak Repetitive Reverse Voltage	V_{RM}	40	V
RMS Reverse Voltage	$V_{R(RMS)}$	28	V
DC Reverse Voltage	V_R	20	V
Peak Forward Current	I_{FSM}	3	A
Mean Rectifying Current	I_O	0.5	A
Power Dissipation	P_D	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	500	$^{\circ}\text{C/W}$
Operating Temperature	T_J	-55~+125	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55~+150	$^{\circ}\text{C}$

Electrical Characteristics ($T_a=25^{\circ}\text{C}$ unless otherwise specified)						
Parameter	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage	V_R	$I_R=100\mu\text{A}$	20	—	—	V
Forward Voltage	V_{F1}	$I_F=10\text{mA}$	—	—	0.3	V
	V_{F2}	$I_F=500\text{mA}$	—	—	0.5	V
Reverse Current	I_R	$V_R=10\text{V}$	—	—	30	μA
Capacitance Between Terminals	C_T	$V_R=10\text{V}, f=1\text{MHz}$	—	20	—	pF



Typical Characteristics

